## **EU2BG THRU EU2JG**

# ULTRAFAST EFFICIENT PLASTIC SILICON RECTIFIER

VOLTAGE:100 TO 600V CURRENT: 1.0A



### **FEATURE**

Low power loss
High surge capability
Glass passivated chip junction
Ultra-fast recovery time for high efficiency
High temperature soldering guaranteed
250 °C/10sec/0.375" lead length at 5 lbs tension

## **MECHANICAL DATA**

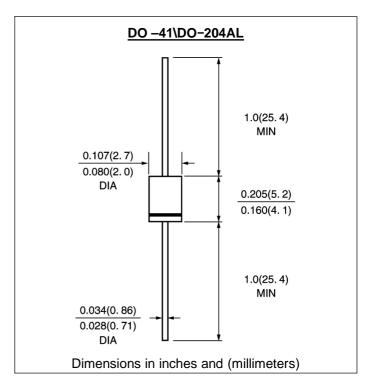
Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C

Case: Molded with UL-94 Class V-0 recognized Flame

Retardant Epoxy

Polarity: color band denotes cathode

Mounting position: any



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

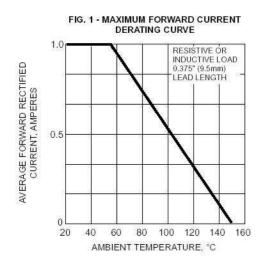
	SYMBOL	EU2BG	EU2DG	EU2GG	EU2JG	units
Maximum Recurrent Peak Reverse Voltage	Vrrm	100	200	400	600	V
Maximum RMS Voltage	Vrms	70	140	280	420	V
Maximum DC blocking Voltage	Vdc	100	200	400	600	V
Maximum Average Forward Rectified Current 3/8"lead length at Ta =55°C	If(av)	1.2 1.0				А
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load	Ifsm	30				А
Maximum Forward Voltage at rated Forward Current and 25°C	Vf	0.9 (IF=1.2A) 1.4 (IF=1.0A)				V
Maximum DC Reverse Current at rated DC blocking voltage $Ta = 25^{\circ}C$ $Ta = 125^{\circ}C$	lr	10 50				μA μA
Maximum Reverse Recovery Time (Note 1)	Trr	50 75			nS	
Typical Junction Capacitance (Note 2)	Cj	17 15			pF	
Typical Thermal Resistance (Note 3)	R(ja)	50 60			60	°C /W
Storage and Operating Temperature Range	Tstg, Tj	-65 to +175				°C

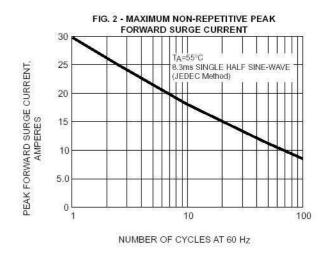
#### Note:

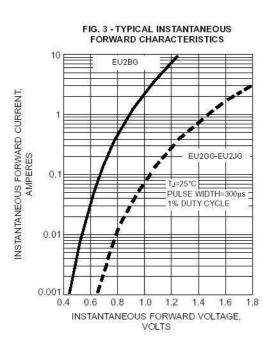
- 1. Reverse Recovery Condition If =0.5A, Ir =1.0A, Irr =0.25A
- 2. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
- 3. Thermal Resistance from Junction to Ambient at 3/8"lead length, P.C. Board Mounted

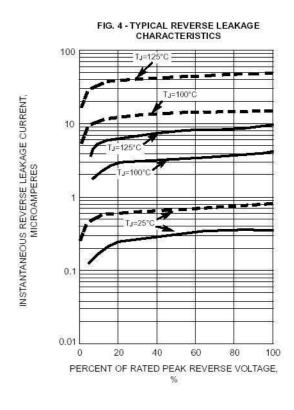
Rev.A1 www.gulfsemi.com

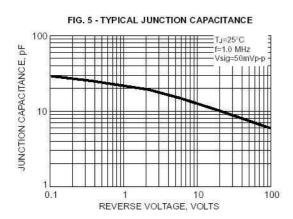
#### RATINGS AND CHARACTERISTIC CURVES EU2BG THRU EU2JG











<sup>1</sup> Rev.A1 www.gulfsemi.com